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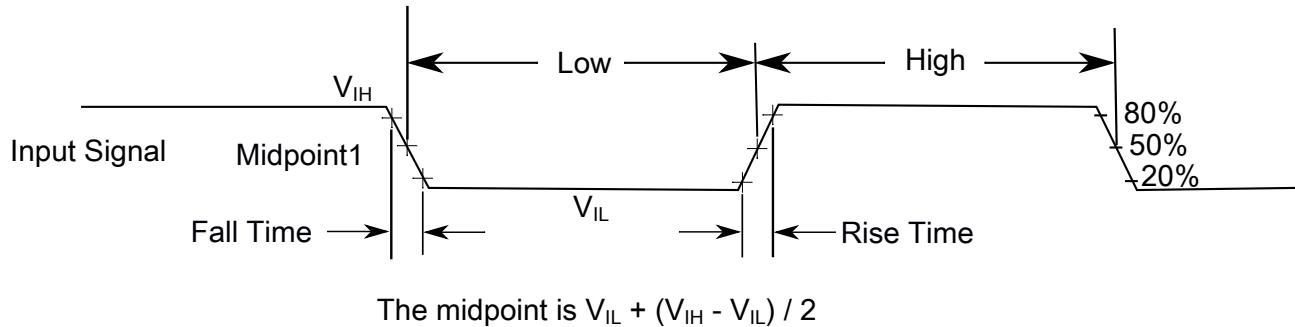
What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	100
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 5x12b, 3x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk26fn2m0vlq18

**Figure 2. Input signal measurement reference**

2.2 Nonswitching electrical specifications

2.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage	0.7 × V_{DD} 0.75 × V_{DD}	— —	V V	
	<ul style="list-style-type: none"> • $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$ • $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$ 				
V_{IL}	Input low voltage	— —	0.35 × V_{DD} 0.3 × V_{DD}	V V	
	<ul style="list-style-type: none"> • $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$ • $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$ 				
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICDIO}	Digital ¹ input pin negative DC injection current (except RTC_WAKEUP pins) — single pin • $V_{IN} < V_{SS}-0.3\text{V}$	-5	—	mA	²
I_{ICAIO}	Analog ¹ input pin DC injection current — single pin • $V_{IN} < V_{SS}-0.3\text{V}$ (Negative current injection)	-5	—	mA	²
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents of 16 contiguous pin	-25	—	mA	

Table continues on the next page...

Table 4. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• $V_{SS} \leq V_{IN} \leq V_{DD}$					
I _{OZ_RTC_WAKEUP}	Hi-Z (off-state) leakage current (per RTC_WAKEUP pin)	—	—	0.25	µA	
R _{PU}	Internal pullup resistors	20	—	50	kΩ	2
R _{PD}	Internal pulldown resistors	20	—	50	kΩ	3

1. Measured at VDD=3.6V
2. Measured at V_{DD} supply voltage = V_{DD} min and Vin = V_{SS}
3. Measured at V_{DD} supply voltage = V_{DD} min and Vin = V_{DD}

2.2.4 Power mode transition operating behaviors

All specifications except t_{POR}, and VLLSx → RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 100MHz
- Bus clock = 50MHz
- FlexBus clock = 50 MHz
- Flash clock = 25 MHz
- MCG mode=FEI

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t _{POR}	After a POR event, amount of time from the point V _{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	300	µs	
	• VLLS0 → RUN	—	172	µs	
	• VLLS1 → RUN	—	172	µs	
	• VLLS2 → RUN	—	94	µs	
	• VLLS3 → RUN	—	94	µs	
	• LLS2 → RUN	—	5.8	µs	
	• LLS3 → RUN	—	5.8	µs	
	• VLPS → RUN	—	5.4	µs	
	• STOP → RUN	—	5.4	µs	

General

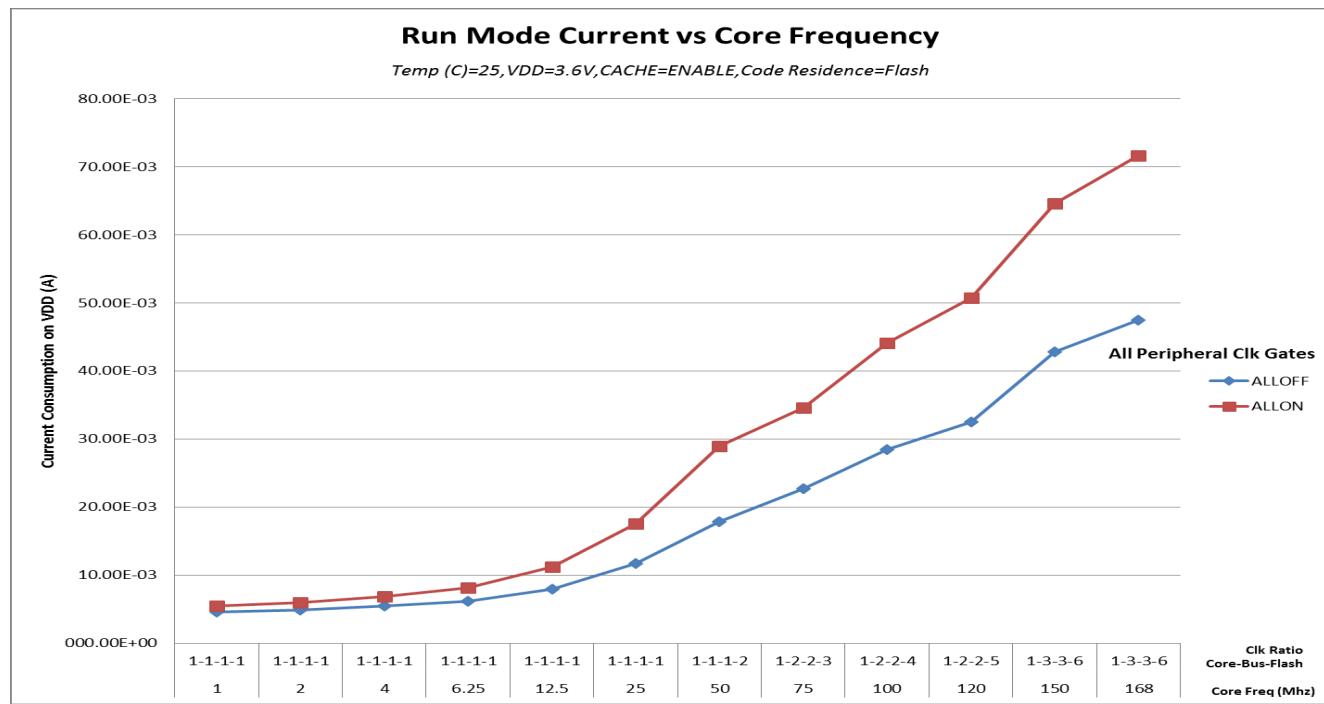


Figure 3. Run mode supply current vs. core frequency

Table 11. General switching specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
	<ul style="list-style-type: none"> • $1.71 \leq V_{DD} \leq 2.7V$ • $2.7 \leq V_{DD} \leq 3.6V$ 	—	7	ns	
	Port rise and fall time (low drive strength) <ul style="list-style-type: none"> Slew enabled <ul style="list-style-type: none"> • $1.71 \leq V_{DD} \leq 2.7V$ • $2.7 \leq V_{DD} \leq 3.6V$ Slew disabled <ul style="list-style-type: none"> • $1.71 \leq V_{DD} \leq 2.7V$ • $2.7 \leq V_{DD} \leq 3.6V$ 	—	25	ns	5
		—	15	ns	
		—	7	ns	
		—	7	ns	

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.
3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
4. 75 pF load
5. 15 pF load

2.4 Thermal specifications

2.4.1 Thermal operating requirements

Table 12. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature <ul style="list-style-type: none"> • For BGA and LQFP package 	-40	125	°C	
T_J	Die junction temperature <ul style="list-style-type: none"> • For CSP package 	-40	95	°C	
T_A	Ambient temperature <ul style="list-style-type: none"> • For BGA and LQFP package 	-40	105	°C	1
T_A	Ambient temperature <ul style="list-style-type: none"> • For CSP package 	-40	85	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed maximum T_J . The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times \text{chip power dissipation}$.

3.1.2 JTAG electricals

Table 14. JTAG limited voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	TCLK frequency of operation <ul style="list-style-type: none"> • Boundary Scan • JTAG and CJTAG • Serial Wire Debug 	0	10	MHz
		0	25	
		0	50	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width <ul style="list-style-type: none"> • Boundary Scan • JTAG and CJTAG • Serial Wire Debug 	50	—	ns
		20	—	ns
		10	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	2.0	—	ns
J7	TCLK low to boundary scan output data valid	—	28	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	19	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8	—	ns

Table 15. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation <ul style="list-style-type: none"> • Boundary Scan • JTAG and CJTAG • Serial Wire Debug 	0	10	MHz
		0	20	
		0	40	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width <ul style="list-style-type: none"> • Boundary Scan 	50	—	ns

Table continues on the next page...

Table 16. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
D _{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t _{pll_lock}	Lock detector detection time	—	—	150 × 10 ⁻⁶ + 1075(1/ f _{pll_ref})	s	10

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. This applies when SCTRIM at value (0x80) and SCFTRIM control bit at value (0x0).
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
4. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
8. Excludes any oscillator currents that are also consuming power while PLL is in operation.
9. This specification was obtained using a NXP developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
10. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

3.3.2 IRC48M specifications

Table 17. IRC48M specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{DD}	Supply voltage	1.71	—	3.6	V	
I _{DD48M}	Supply current	—	520	—	µA	
f _{irc48m}	Internal reference frequency	—	48	—	MHz	
Δf _{irc48m.ol_lv}	Open loop total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over full temperature <ul style="list-style-type: none"> • Regulator disable (USB_CLK_RECOVER_IRC_EN[REG_EN]=0) • Regulator enable (USB_CLK_RECOVER_IRC_EN[REG_EN]=1) 	—	± 0.4	± 1.0	%f _{irc48m}	1
Δf _{irc48m.ol_hv}	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over 0—70°C <ul style="list-style-type: none"> • Regulator enable (USB_CLK_RECOVER_IRC_EN[REG_EN]=1) 	—	± 0.2	± 0.5	%f _{irc48m}	1
Δf _{irc48m.ol_hv}	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over full temperature	—	± 0.4	± 1.0	%f _{irc48m}	1

Table continues on the next page...

Table 20. 32kHz oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp}^1	Peak-to-peak amplitude of oscillation	—	0.6	—	V

- When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.4.2 32 kHz oscillator frequency specifications

Table 21. 32 kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$f_{\text{osc_lo}}$	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$f_{\text{ec_extal32}}$	Externally provided input clock frequency	—	32.768	—	kHz	2
$V_{\text{ec_extal32}}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

- Proper PC board layout procedures must be followed to achieve specifications.
- This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
- The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT} .

3.4 Memories and memory interfaces

3.4.1 Flash (FTFE) electrical specifications

This section describes the electrical characteristics of the FTFE module.

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 22. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm8}	Program Phrase high-voltage time	—	7.5	18	μs	
t_{hversscr}	Erase Flash Sector high-voltage time	—	13	113	ms	1
$t_{\text{hversblk256k}}$	Erase Flash Block high-voltage time for 256 KB	—	208	1808	ms	1
$t_{\text{hversblk512k}}$	Erase Flash Block high-voltage time for 512 KB	—	416	3616	ms	1

Peripheral operating requirements and behaviors

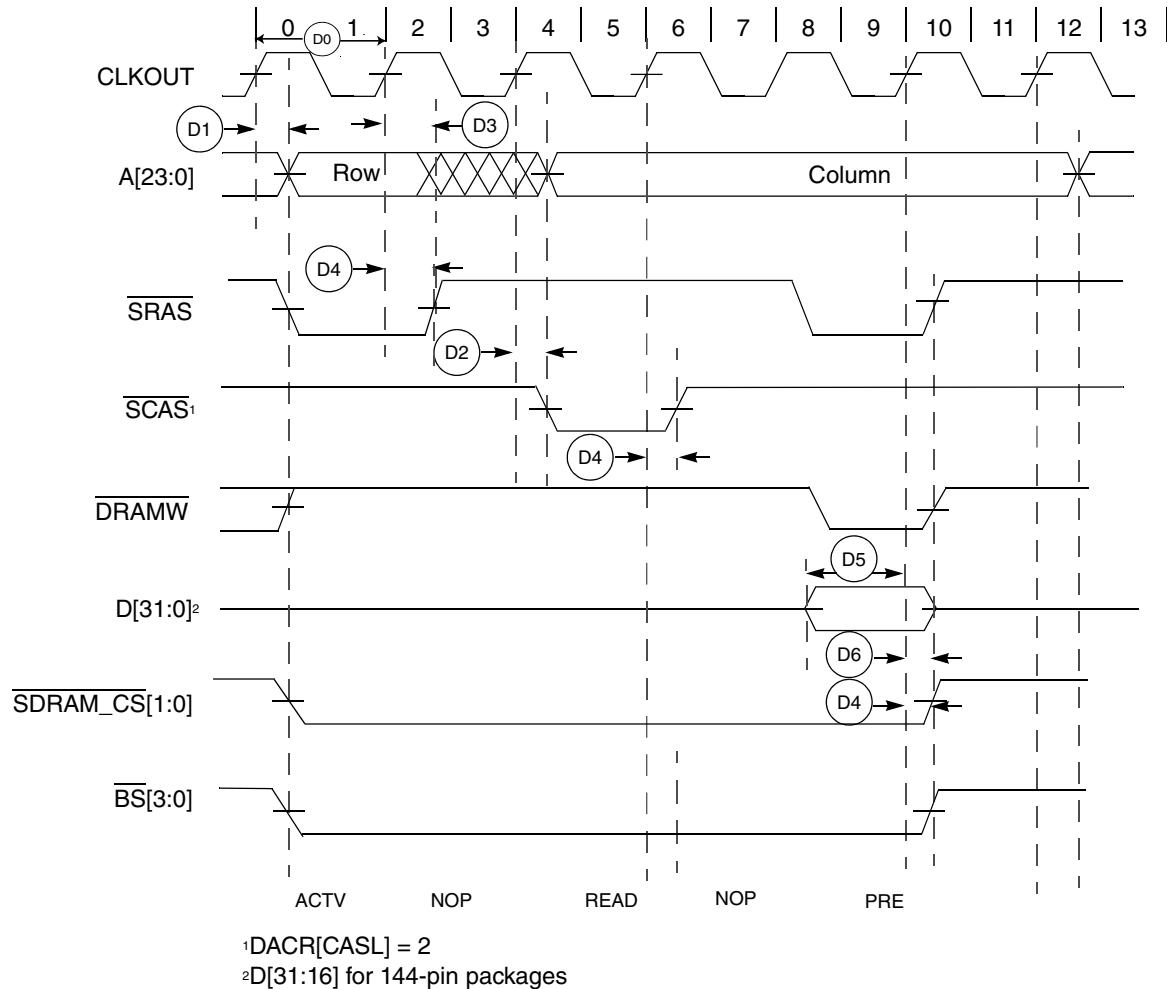


Figure 15. SDRAM read timing diagram

Table 29. SDRAM Timing (Full voltage range)

NUM	Characteristic ¹	Symbol	Min	Max	Unit
	Operating voltage	1.71	3.6	V	
	Frequency of operation	—	CLKOUT	MHz	
D0	Clock period	1/CLKOUT	—	ns	²
D1	CLKOUT high to SDRAM address valid	t _{CHDAV}	-	11.2	ns
D2	CLKOUT high to SDRAM control valid	t _{CHDCV}		11.1	ns
D3	CLKOUT high to SDRAM address invalid	t _{CHDAI}	1.0	-	ns
D4	CLKOUT high to SDRAM control invalid	t _{CHDCI}	1.0	-	ns
D5	SDRAM data valid to CLKOUT high	t _{DDVCH}	12.0	-	ns
D6	CLKOUT high to SDRAM data invalid	t _{CHDDI}	1.0	-	ns
D7 ³	CLKOUT high to SDRAM data valid	t _{CHDDVW}	-	12.0	ns
D8 ³	CLKOUT high to SDRAM data invalid	t _{CHDDIW}	1.0	-	ns

- All timing specifications are based on taking into account, a 25pF load on the SDRAM output pins.

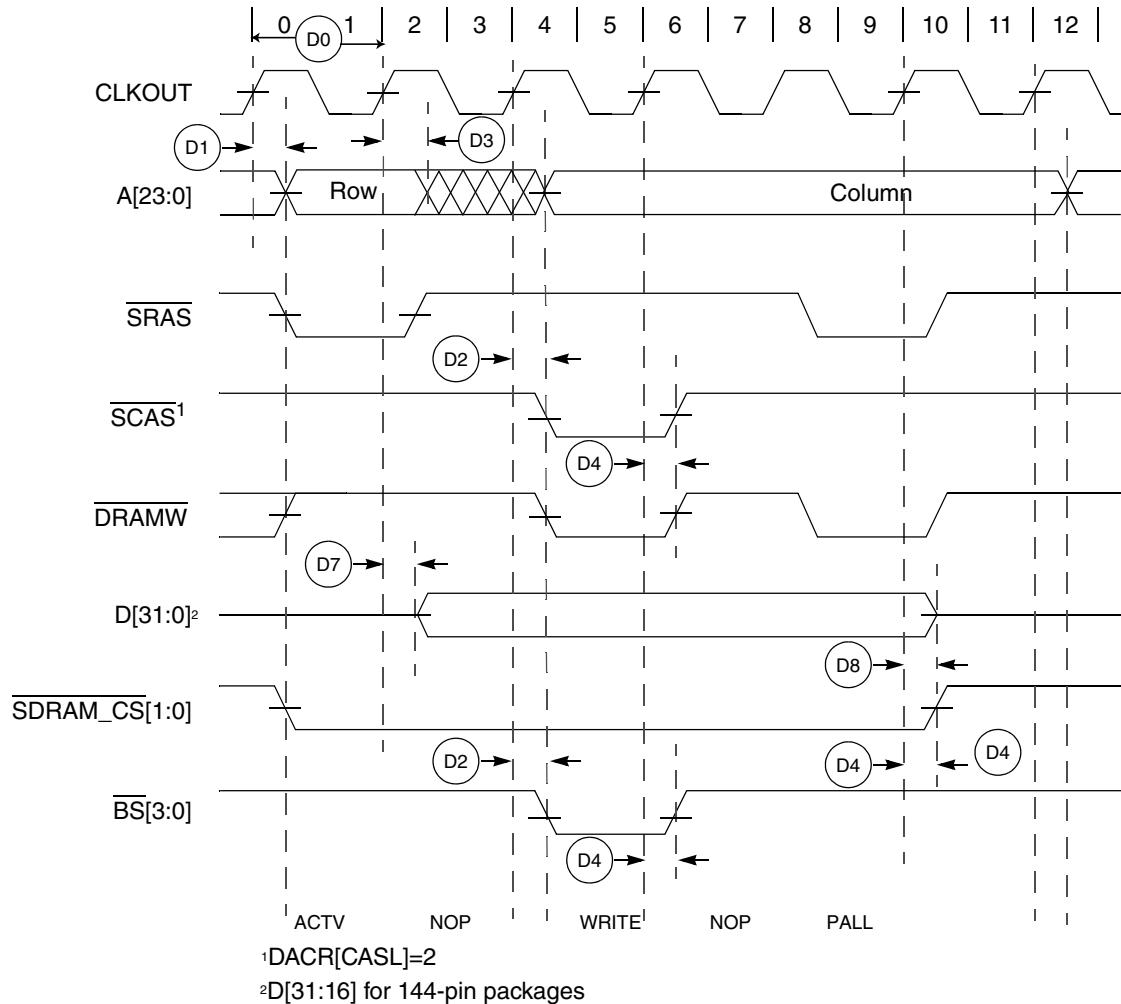


Figure 16. SDRAM write timing diagram

3.5 Analog

3.5.1 ADC electrical specifications

The 16-bit accuracy specifications listed in [Table 31](#) and [Table 32](#) are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

3.5.2 CMP and 6-bit DAC electrical specifications

Table 33. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
V_{AIN}	Analog input voltage	$V_{SS} - 0.3$	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	$V_{DD} - 0.5$	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	—	—	40	μs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	-0.5	—	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to $V_{DD} - 0.6$ V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}/64$

3.7.3 USB DCD electrical specifications

Table 41. USB DCD electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DP_SRC} , V_{DM_SRC}	USB_DP and USB_DM source voltages (up to 250 μ A)	0.5	—	0.7	V
V_{LGC}	Threshold voltage for logic high	0.8	—	2.0	V
I_{DP_SRC}	USB_DP source current	7	10	13	μ A
I_{DM_SINK} , I_{DP_SINK}	USB_DM and USB_DP sink currents	50	100	150	μ A
R_{DM_DWN}	D-pulldown resistance for data pin contact detect	14.25	—	24.8	k Ω
V_{DAT_REF}	Data detect voltage	0.25	0.33	0.4	V

3.7.4 CAN switching specifications

See [General switching specifications](#).

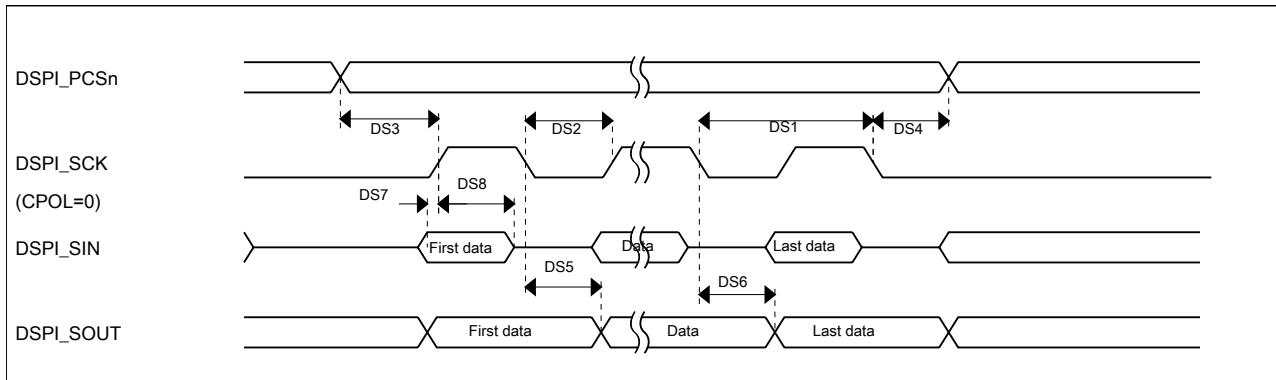
3.7.5 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 42. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	30	MHz	
DS1	DSPI_SCK output cycle time	$2 \times t_{BUS}$	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns	
DS3	DSPI_PCSn valid to DSPI_SCK delay	$(t_{BUS} \times 2) - 2$	—	ns	1
DS4	DSPI_SCK to DSPI_PCSn invalid delay	$(t_{BUS} \times 2) - 2$	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	15.0	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	1.0	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	15.8	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

**Figure 24. DSPI classic SPI timing — master mode****Table 43. Slave mode DSPI timing (limited voltage range)**

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		15 ¹	MHz
DS9	DSPI_SCK input cycle time	$4 \times t_{BUS}$	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	23.0	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_IN to DSPI_SCK input setup	2.7	—	ns
DS14	DSPI_SCK to DSPI_IN input hold	7.0	—	ns
DS15	DSPI_SS active to DSPI_SOUT driven	—	13	ns
DS16	DSPI_SS inactive to DSPI_SOUT not driven	—	13	ns

1. The maximum operating frequency is measured with non-continuous CS and SCK. When DSPI is configured with continuous CS and SCK, there is a constraint that SPI clock should not be greater than 1/6 of bus clock, for example, when bus clock is 60MHz, SPI clock should not be greater than 10MHz.

**Table 48. SDHC full voltage range switching specifications
(continued)**

Num	Symbol	Description	Min.	Max.	Unit
Card input clock					
SD1	f _{pp}	Clock frequency (low speed)	0	400	kHz
	f _{pp}	Clock frequency (SD\SDIO full speed\high speed)	0	25\50	MHz
	f _{pp}	Clock frequency (MMC full speed\high speed)	0	20\50	MHz
	f _{OD}	Clock frequency (identification mode)	0	400	kHz
SD2	t _{WL}	Clock low time	7	—	ns
SD3	t _{WH}	Clock high time	7	—	ns
SD4	t _{TLH}	Clock rise time	—	3	ns
SD5	t _{THL}	Clock fall time	—	3	ns
SDHC output / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD6	t _{OD}	SDHC output delay (output valid)	-5	8.6 8.3	ns
SDHC input / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD7	t _{ISU}	SDHC input setup time	5	—	ns
SD8	t _{IH}	SDHC input hold time	0	—	ns

Table 49. SDHC limited voltage range switching specifications

Num	Symbol	Description	Min.	Max.	Unit
		Operating voltage	2.7	3.6	V
Card input clock					
SD1	f _{pp}	Clock frequency (low speed)	0	400	kHz
	f _{pp}	Clock frequency (SD\SDIO full speed\high speed)	0	25\50	MHz
	f _{pp}	Clock frequency (MMC full speed\high speed)	0	20\50	MHz
	f _{OD}	Clock frequency (identification mode)	0	400	kHz
SD2	t _{WL}	Clock low time	7	—	ns
SD3	t _{WH}	Clock high time	7	—	ns
SD4	t _{TLH}	Clock rise time	—	3	ns
SD5	t _{THL}	Clock fall time	—	3	ns
SDHC output / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD6	t _{OD}	SDHC output delay (output valid)	-5	7.6 8.3	ns
SDHC input / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD7	t _{ISU}	SDHC input setup time	5	—	ns
SD8	t _{IH}	SDHC input hold time	0	—	ns

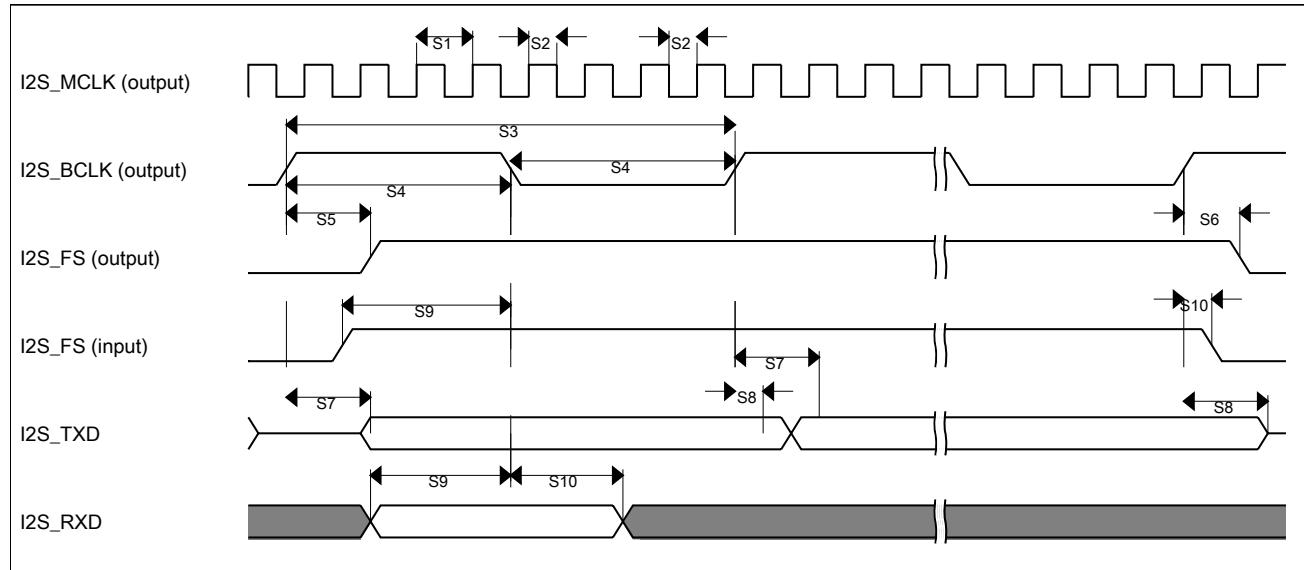


Figure 30. I²S timing — master mode

Table 51. I2S slave mode timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S11	I2S_BCLK cycle time (input)	80	—	ns
S12	I2S_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_FS input setup before I2S_BCLK	4.5	—	ns
S14	I2S_FS input hold after I2S_BCLK	2	—	ns
S15	I2S_BCLK to I2S_TXD/I2S_FS output valid	—	20	ns
S16	I2S_BCLK to I2S_TXD/I2S_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_BCLK	4.5	—	ns
S18	I2S_RXD hold after I2S_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹		25	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

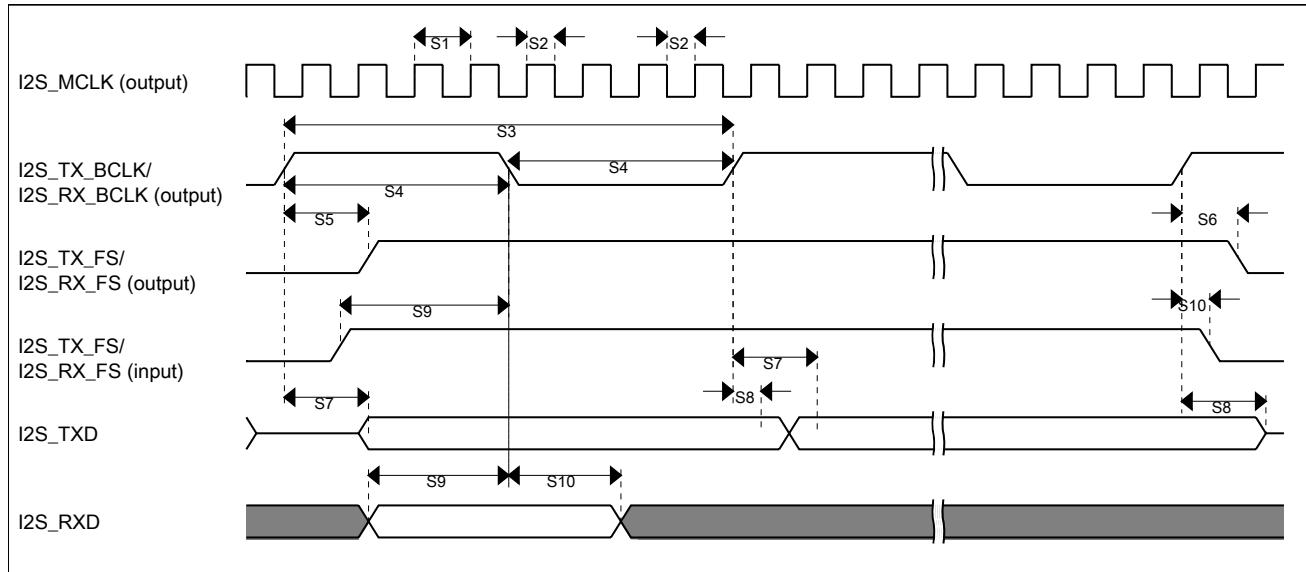


Figure 32. I2S/SAI timing — master modes

Table 53. I2S/SAI slave mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	4.5	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	23.1	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	4.5	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	25	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

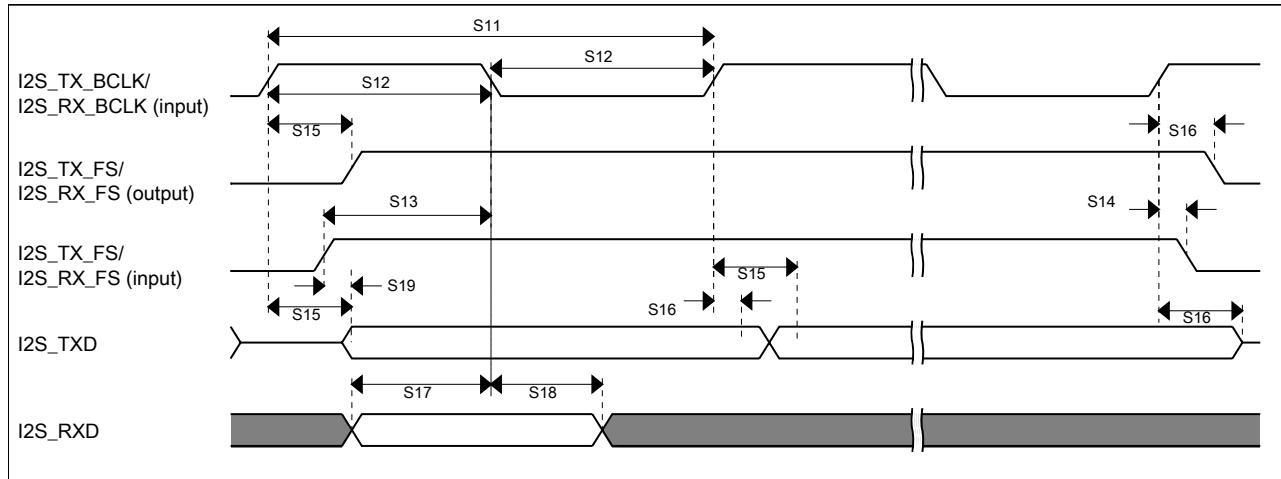


Figure 33. I2S/SAI timing — slave modes

3.7.11.2 VLPR, VLPW, and VLPS mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in VLPR, VLPW, and VLPS modes.

Table 54. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/I2S_RX_FS output valid	—	45	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	45	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	45	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

169 CSP	169 BGA	144 LQFP	144 BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EPORT
H4	G13	81	H10	PTB0/ LLWU_P5	ADC0_SE8/ ADC1_SE8/ TSIO_CH0	ADC0_SE8/ ADC1_SE8/ TSIO_CH0	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0		SDRAM_CAS_b	FTM1_QD_PHB/ TPM1_CH0		
J2	G12	82	H9	PTB1	ADC0_SE9/ ADC1_SE9/ TSIO_CH6	ADC0_SE9/ ADC1_SE9/ TSIO_CH6	PTB1	I2C0_SDA	FTM1_CH1		SDRAM_RAS_b	FTM1_QD_PHB/ TPM1_CH1		
J1	G11	83	G12	PTB2	ADC0_SE12/ TSIO_CH7	ADC0_SE12/ TSIO_CH7	PTB2	I2C0_SCL	UART0 RTS_b		SDRAM_WE	FTM0_FLT3		
H3	G10	84	G11	PTB3	ADC0_SE13/ TSIO_CH8	ADC0_SE13/ TSIO_CH8	PTB3	I2C0_SDA	UART0 CTS_b/ UART0 COL_b		SDRAM_CS0_b	FTM0_FLT0		
G7	—	—	—	VSS	VSS	VSS								
G6	—	—	—	VDD	VDD	VDD								
H2	H9	85	G10	PTB4	ADC1_SE10	ADC1_SE10	PTB4				SDRAM_CS1_b	FTM1_FLT0		
H1	F13	86	G9	PTB5	ADC1_SE11	ADC1_SE11	PTB5					FTM2_FLT0		
G5	F12	87	F12	PTB6	ADC1_SE12	ADC1_SE12	PTB6				FB_AD23/ SDRAM_D23			
G4	F11	88	F11	PTB7	ADC1_SE13	ADC1_SE13	PTB7				FB_AD22/ SDRAM_D22			
G3	F10	89	F10	PTB8	DISABLED		PTB8		UART3 RTS_b		FB_AD21/ SDRAM_D21			
G2	F9	90	F9	PTB9	DISABLED		PTB9	SPI1_PCS1	UART3 CTS_b		FB_AD20/ SDRAM_D20			
G1	G9	91	E12	PTB10	ADC1_SE14	ADC1_SE14	PTB10	SPI1_PCS0	UART3_RX		FB_AD19/ SDRAM_D19	FTM0_FLT1		
F5	E13	92	E11	PTB11	ADC1_SE15	ADC1_SE15	PTB11	SPI1_SCK	UART3_TX		FB_AD18/ SDRAM_D18	FTM0_FLT2		
F4	E12	—	—	PTB12	DISABLED		PTB12	UART3 RTS_b	FTM1_CH0	FTM0_CH4	FB_A9/ SDRAM_D9	FTM1_QD_PHB/ TPM1_CH0		
F3	E11	—	—	PTB13	DISABLED		PTB13	UART3 CTS_b	FTM1_CH1	FTM0_CH5	FB_A8/ SDRAM_D8	FTM1_QD_PHB/ TPM1_CH1		
F2	E10	—	—	PTB14	DISABLED		PTB14	CAN1_TX			FB_A7/ SDRAM_D7			
F1	E9	—	—	PTB15	DISABLED		PTB15	CAN1_RX			FB_A6/ SDRAM_D6			
—	—	93	H7	VSS	VSS	VSS								

Pinout

169 CSP	169 BGA	144 LQFP	144 BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EZPORT
—	—	94	F5	VDD	VDD									
E1	F8	95	E10	PTB16	TSI0_CH9	TSI0_CH9	PTB16	SPI1_SOUT	UART0_RX	FTM_CLKIN0	FB_AD17/SDRAM_D17	EWM_IN	TPM_CLKIN0	
E2	D13	96	E9	PTB17	TSI0_CH10	TSI0_CH10	PTB17	SPI1_SIN	UART0_TX	FTM_CLKIN1	FB_AD16/SDRAM_D16	EWM_OUT_b	TPM_CLKIN1	
E3	D12	97	D12	PTB18	TSI0_CH11	TSI0_CH11	PTB18	CAN0_TX	FTM2_CH0	I2S0_TX_BCLK	FB_AD15/SDRAM_A23	FTM2_QD_PHA TPM2_CH0		
E4	D11	98	D11	PTB19	TSI0_CH12	TSI0_CH12	PTB19	CAN0_RX	FTM2_CH1	I2S0_TX_FS	FB_OE_b	FTM2_QD_PHB TPM2_CH1		
E5	D10	99	D10	PTB20	DISABLED		PTB20	SPI2_PCS0			FB_AD31/SDRAM_D31	CMP0_OUT		
D1	D9	100	D9	PTB21	DISABLED		PTB21	SPI2_SCK			FB_AD30/SDRAM_D30	CMP1_OUT		
D2	C13	101	C12	PTB22	DISABLED		PTB22	SPI2_SOUT			FB_AD29/SDRAM_D29	CMP2_OUT		
D3	C12	102	C11	PTB23	DISABLED		PTB23	SPI2_SIN	SPI0_PCS5		FB_AD28/SDRAM_D28	CMP3_OUT		
C1	B13	103	B12	PTC0	ADC0_SE14/TSI0_CH13	ADC0_SE14/TSI0_CH13	PTC0	SPI0_PCS4	PDB0_EXTRG	USB0_SOF_OUT	FB_AD14/SDRAM_A22	I2S0_TXD1		
C2	B12	104	B11	PTC1/LLWU_P6	ADC0_SE15/TSI0_CH14	ADC0_SE15/TSI0_CH14	PTC1/LLWU_P6	SPI0_PCS3	UART1_RTS_b	FTM0_CH0	FB_AD13/SDRAM_A21	I2S0_TXD0		
D4	A13	105	A12	PTC2	ADC0_SE4b/CMP1_IN0/TSI0_CH15	ADC0_SE4b/CMP1_IN0/TSI0_CH15	PTC2	SPI0_PCS2	UART1_CTS_b	FTM0_CH1	FB_AD12/SDRAM_A20	I2S0_TX_FS		
B1	A12	106	A11	PTC3/LLWU_P7	CMP1_IN1	CMP1_IN1	PTC3/LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2	CLKOUT	I2S0_TX_BCLK		
F6	C11	107	H8	VSS	VSS	VSS								
E6	H6	108	—	VDD	VDD	VDD								
A1	B11	109	A9	PTC4/LLWU_P8	DISABLED		PTC4/LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3	FB_AD11/SDRAM_A19	CMP1_OUT		
B2	A11	110	D8	PTC5/LLWU_P9	DISABLED		PTC5/LLWU_P9	SPI0_SCK	LPTMR0_ALT2	I2S0_RXD0	FB_AD10/SDRAM_A18	CMP0_OUT	FTM0_CH2	
C3	A10	111	C8	PTC6/LLWU_P10	CMPO_IN0	CMPO_IN0	PTC6/LLWU_P10	SPI0_SOUT	PDB0_EXTRG	I2S0_RX_BCLK	FB_AD9/SDRAM_A17	I2S0_MCLK		

Ordering parts

	1	2	3	4	5	6	7	8	9	10	11	12	13
A	PTC4/ LLWU_P8	PTC9	PTC13	PTC15	PTC16	PTC24	PTC27	PTD1	PTD5	PTD7	PTD10	PTD13	PTE1/ LLWU_P0
B	PTC3/ LLWU_P7	PTC5/ LLWU_P9	PTC10	PTC14	PTC17	PTC19	PTC28	PTD2/ LLWU_P13	PTD6/ LLWU_P15	PTD9	PTD14	PTE2/ LLWU_P1	PTE3
C	PTC0	PTC1/ LLWU_P6	PTC6/ LLWU_P10	PTC8	PTC12	PTC18	PTC29	PTD3	PTD8/ LLWU_P24	PTD12	PTE0	PTE4/ LLWU_P2	PTE6/ LLWU_P16
D	PTB21	PTB22	PTB23	PTC2	PTC7	PTC11/ LLWU_P11	PTC25	PTD0/ LLWU_P12	PTD11/ LLWU_P25	PTD15	PTE5	PTE8	PTE9/ LLWU_P17
E	PTB16	PTB17	PTB18	PTB19	PTB20	VDD	VDD	PTC26	VDD	PTE7	PTE11	PTE12	VDD
F	PTB15	PTB14	PTB13	PTB12	PTB11	VSS	VSS	PTD4/ LLWU_P14	VDD	PTE10/ LLWU_P18	PTE17/ LLWU_P19	PTE19	VSS
G	PTB10	PTB9	PTB8	PTB7	PTB6	VDD	VSS	PTE16	PTE18/ LLWU_P20	VREG_OUT	VREG_IN0	USB0_DP	
H	PTB5	PTB4	PTB3	PTB0/ LLWU_P5	PTA31	VSS	VSS	NC	NC	ADC1_SE16/ CMP2_IN2/ ADC0_SE22	VREG_IN1	USB0_DM	
J	PTB2	PTB1	PTA26	PTA25	PTA9	PTA3	PTE27	NC	NC	RTC_WAKEUP_B	ADC1_DP1	USB1_VSS	USB1_DP
K	PTA30	PTA29	PTA24	PTA16	PTA10/ LLWU_P22	PTA4/ LLWU_P3	PTE28	VDD	NC	ADC0_SE16/ CMP1_IN2/ ADC0_SE21	ADC1_DM1	USB1_VBUS	USB1_DM
L	PTA28	PTA27	PTA17	PTA15	PTA13/ LLWU_P4	PTA7	PTA2	PTE26/ CLKOUT32	VBAT	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VDDA	ADC1_DP0/ ADC0_DP3	ADC0_DP0/ ADC1_DP3
M	RESET_b	VSS	VDD	PTA12	PTA8	VDD	PTA1	PTE25/ LLWU_P21	XTAL32	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	VREFH	ADC1_DM0/ ADC0_DM3	ADC0_DM0/ ADC1_DM3
N	PTA18	PTA19	PTA14	PTA11/ LLWU_P23	PTA6	PTA5	PTA0	PTE24	EXTAL32	NC	DAC1_OUT/ CMP0_IN4/ CMP2_IN3/ ADC1_SE23	VREFL	VSSA
	1	2	3	4	5	6	7	8	9	10	11	12	13

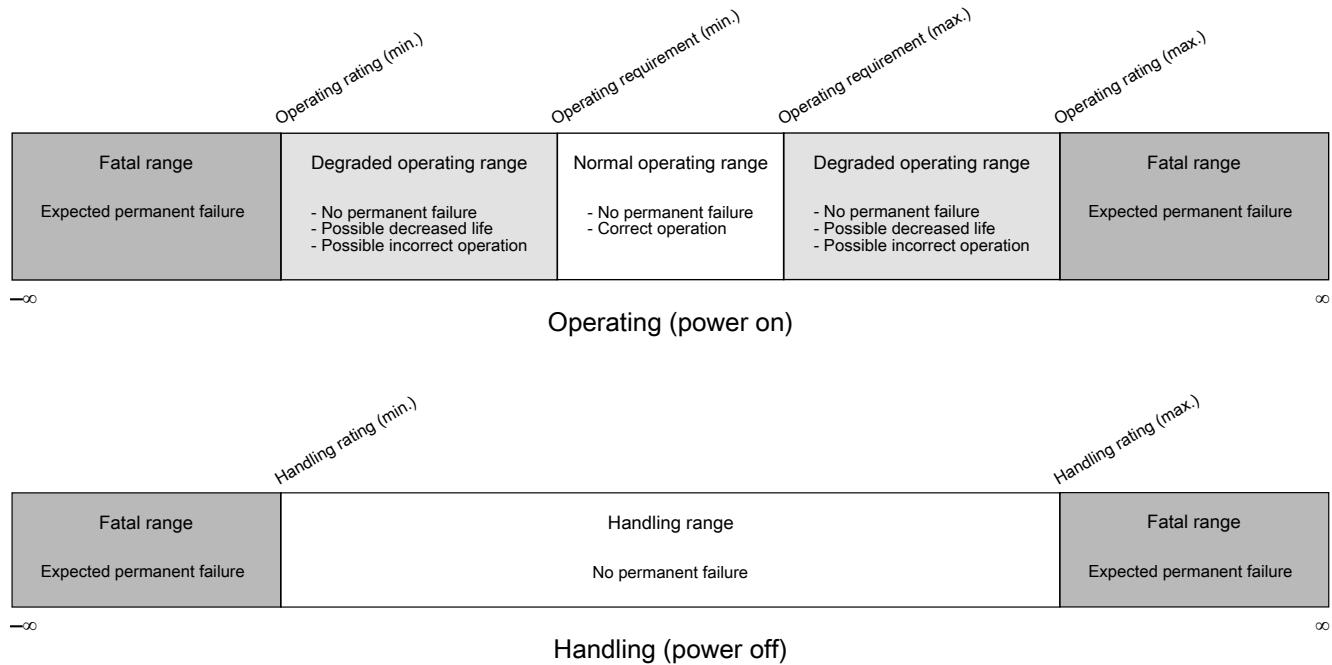
Figure 39. MK26 169 CSP Pinout Diagram

6 Ordering parts

Revision History

Symbol	Description	Value	Unit
T _A	Ambient temperature	25	°C
V _{DD}	Supply voltage	3.3	V

8.4 Relationship between ratings and operating requirements



8.5 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

9 Revision History

The following table provides a revision history for this document.